

CMOS Digital Integrated Circuits Silicon Monolithic

74VHC4051AFT,74VHC4052AFT,74VHC4053AFT

1. Functional Description

74VHC4051AFT:8-Channel Analog Multiplexer/Demultiplexer 74VHC4052AFT:Dual 4-Channel Analog Multiplexer/Demultiplexer 74VHC4053AFT:Triple 2-Channel Analog Multiplexer/Demultiplexer

2. General

The 74VHC4051AFT, 74VHC4052AFT and 74VHC4053AFT are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

The 74VHC4051AFT, 74VHC4052AFT and 74VHC4053AFT offer analog/digital signal selection as well as mixed signals. The 74VHC4051AFT has an 8-channel configuration, the 74VHC4052AFT has an 4-channel $\times 2$ configuration, and the 74VHC4053AFT has a 2-channel $\times 3$ configuration.

The switches for each channel are turned ON by the control pin digital signals.

All control inputs are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the V_{CC}). As a result, for example, 5.5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the 74VHC4051AFT, 74VHC4052AFT and 74VHC4053AFT can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.

3. Features

- (1) AEC-Q100 (Rev. H) (Note 1)
- (2) Wide operating temperature range: $T_{opr} = -40$ to 125 °C
- (3) Low ON-resistance: $R_{ON} = 45 \Omega$ (typ.) ($V_{CC} = 3.0 \text{ V}$)

$$R_{ON} = 24 \Omega \text{ (typ.) } (V_{CC} = 4.5 \text{ V})$$

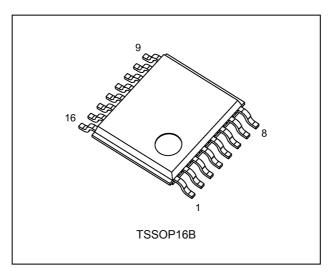
- (4) Low power dissipation: $I_{CC} = 2.0 \mu A \text{ (max) (} T_a = 25 \text{°C)}$
- (5) High noise immunity: $V_{IL} = 0.8 \text{ V (max)} V_{CC} = 3.0 \text{ V}$

$$V_{IH} = 2.0 \text{ V (min) } V_{CC} = 3.0 \text{ V}$$

(6) Power down protection is provided on all control inputs.

Note 1: This device is compliant with the reliability requirements of AEC-Q100. For details, contact your Toshiba sales representative.

4. Packaging



Start of commercial production

2013-06

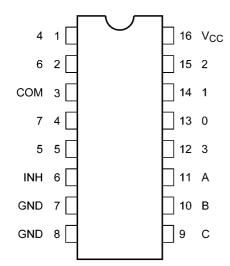
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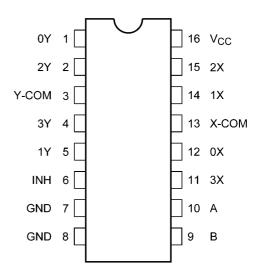


5. Pin Assignment

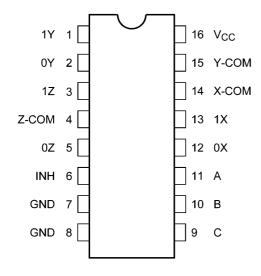
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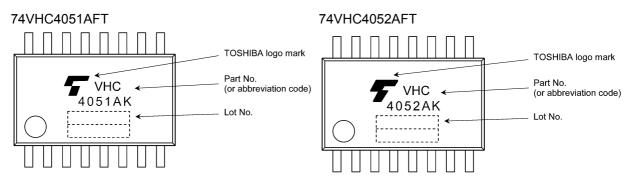


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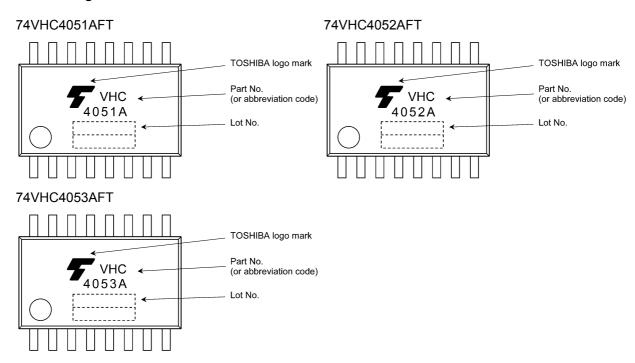
6. Markin

6.1. Marking (Note)



Note: For devices with the ordering part number ending in K.

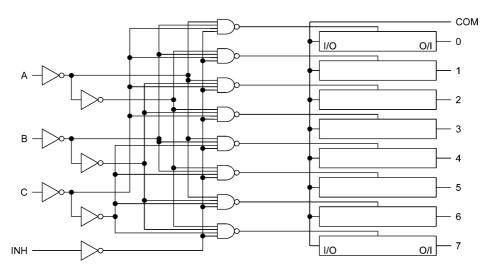
6.2. Marking



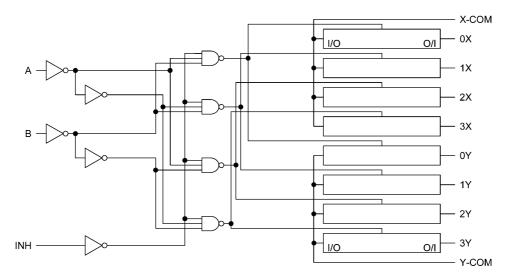


7. System Diagram

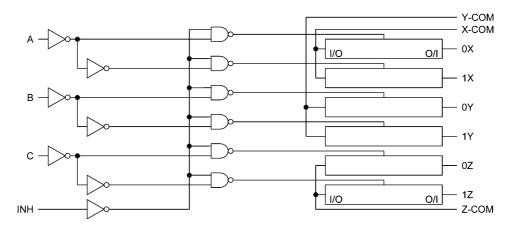
74VHC4051AFT



74VHC4052AFT



74VHC4053AFT





8. Truth Table

Input Inhibit	Input C*	Input B	Input A	ON Channel 74VHC4051AFT	ON Channel 74VHC4052AFT	ON Channel 74VHC4053AFT
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z
L	Н	L	L	4	_	0X, 0Y, 1Z
L	Н	L	Н	5	_	1X, 0Y, 1Z
L	Н	Н	L	6	_	0X, 1Y, 1Z
L	Н	Н	Н	7	_	1X, 1Y, 1Z
Н	Х	Х	Х	None	None	None

X: Don't care

Except 74VHC4052AFT

9. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		-0.5 to 7.0	V
Input voltage	V _{IN}		-0.5 to 7.0	V
Switch I/O voltage	V _{I/O}		-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}		-20	mA
I/O diode current	I _{I/OK}		±25	mA
Switch through current	I _T		±25	mA
V _{CC} /ground current	I _{CC}		±50	mA
Power dissipation	P _D	(Note 1)	180	mW
Storage temperature	T _{stg}		-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: 180 mW in the range of T_a = -40 to 85 °C. From T_a = 85 to 125 °C a derating factor of -3.25 mW/°C shall be applied until 50 mW.

10. Operating Ranges (Note)

Characteristics	Symbol	Test Condition	Rating	Unit
Supply voltage	V _{CC}		2.0 to 5.5	V
Input voltage	V _{IN}		0 to 5.5	V
Switch I/O voltage	Vs		0 to V _{CC}	V
Operating temperature	T _{opr}		-40 to 125	°C
Input rise and fall times	dt/dv	V _{CC} = 2.5 ± 0.2 V	0 to 200	ns/V
		V _{CC} = 3.3 ± 0.3 V	0 to 100	
		V _{CC} = 5 ± 0.5 V	0 to 20	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either V_{CC} or GND.

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11. Electrical Characteristics

11.1. DC Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
High-level input voltage	V _{IH}	_	2.0	1.5	_	_	V
			3.0	2.0	_	_	
			4.5	3.15	_	_	
			5.5	3.85	_	_	
Low-level input voltage	V _{IL}	_	2.0	_	_	0.5	V
			3.0	_	_	0.8	
			4.5	_	_	1.35	
			5.5	_	_	1.65	
ON-resistance	R _{ON}	V _{IN} = V _{IH} or V _{IL}	2.3	_	200	_	Ω
		$V_{I/O} = V_{CC}$ to GND $I_{I/O} = 2 \text{ mA}$	3.0	_	45	86	
			4.5	_	24	37	
		V _{IN} = V _{IH} or V _{IL}	2.3	_	28	73	
		$V_{I/O} = V_{CC}$ or GND $I_{I/O} = 2 \text{ mA}$	3.0	_	22	38	
			4.5	_	17	27	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH} or V _{IL}	2.3	_	10	25	Ω
between switches		$V_{I/O} = V_{CC}$ to GND $I_{I/O} = 2 \text{ mA}$	3.0	_	5	15	
			4.5	_	5	13	
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC}$ or GND $V_{IS} = GND$ to V_{CC} $V_{IN} = V_{IH}$ or V_{IL}	5.5	_	_	±0.1	μА
Input/Output leakage current (Switch ON, Output OPEN)	I _{I/O}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IH}$ or V_{IL}	5.5	_	_	±0.1	μА
Control input leakage current	I _{IN}	V _{IN} = V _{CC} or GND	5.5	_	_	±0.1	μА
Quiescent supply current	I _{CC}	$V_{IN} = V_{CC}$ or GND	5.5	_	_	2.0	μА



11.2. DC Characteristics (Unless otherwise specified, T_a = -40 to 85 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	_	2.0	1.5	_	V
			3.0	2.0	_	
			4.5	3.15	_	
			5.5	3.85	_	
Low-level input voltage	V _{IL}	_	2.0	_	0.50	V
			3.0	_	0.8	
			4.5	_	1.35	
			5.5	_	1.65	
ON-resistance	R _{ON}	V _{IN} = V _{IH} or V _{IL}	2.3	_	_	Ω
		$V_{I/O} = V_{CC}$ to GND $I_{I/O} = 2 \text{ mA}$	3.0	_	108	
		1/0 - 2 IIIA	4.5	_	46	
		V _{IN} = V _{IH} or V _{IL}	2.3	_	84	
		$V_{I/O} = V_{CC}$ or GND $I_{I/O} = 2 \text{ mA}$	3.0	_	44	
		11/0 - 2 11/A	4.5	_	31	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH} or V _{IL}	2.3	_	35	Ω
between switches		$V_{I/O} = V_{CC}$ to GND $I_{I/O} = 2 \text{ mA}$	3.0	_	20	
		11/0 - 2 IIIA	4.5	_	18	
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC}$ or GND $V_{IS} = GND$ to V_{CC} $V_{IN} = V_{IH}$ or V_{IL}	5.5	_	±1.0	μΑ
Input/Output leakage current (Switch ON, Output OPEN)	I _{I/O}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IH}$ or V_{IL}	5.5	_	±1.0	μА
Control input leakage current	I _{IN}	V _{IN} = V _{CC} or GND	5.5		±1.0	μА
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	5.5		20.0	μА

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11.3. DC Characteristics (Unless otherwise specified, T_a = -40 to 125 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	_	2.0	1.5	_	V
			3.0	2.0	_	
			4.5	3.15	_]
			5.5	3.85	_	
Low-level input voltage	V _{IL}	_	2.0	_	0.5	٧
			3.0	_	0.8	
			4.5	_	1.35	
			5.5	_	1.65	
ON-resistance	R _{ON}	V _{IN} = V _{IH} or V _{IL}	2.3	_	_	Ω
		$V_{I/O} = V_{CC}$ to GND $I_{I/O} = 2$ mA	3.0	_	125	
		11/0 - 2 IIIA	4.5	_	54	
		V _{IN} = V _{IH} or V _{IL}	2.3	_	105]
		$V_{I/O} = V_{CC}$ or GND $I_{I/O} = 2 \text{ mA}$	3.0	_	55	
		11/0 - 2 IIIA	4.5	_	39	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH} or V _{IL}	2.3	_	45	Ω
between switches		V _{I/O} = V _{CC} to GND	3.0	_	25]
		$I_{I/O} = 2 \text{ mA}$	4.5	_	23]
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC}$ or GND $V_{IS} = GND$ to V_{CC} $V_{IN} = V_{IH}$ or V_{IL}	5.5	_	±4.0	μА
Input/Output leakage current (Switch ON, Output OPEN)	I _{I/O}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IH}$ or V_{IL}	5.5	_	±4.0	μА
Control input leakage current	I _{IN}	V _{IN} = V _{CC} or GND	5.5		±2.0	μА
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	5.5		40.0	μА



11.4. AC Characteristics (Unless otherwise specified, T_a = 25 °C, Input: t_r = t_f = 3 ns)

Characteristics	Part Number	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Unit
Phase difference between		Φι/Ο		2.5 ± 0.2	15		1.2	10	ns
input to output					50	1	2.6	12	
				3.3 ± 0.3	15	1	0.8	6	
					50	1	1.5	9	
				5.0 ± 0.5	15	1	0.3	4	
					50	١	0.6	6	
Output enable time		t_{PZL}, t_{PZH}	$R_L = 1 k\Omega$	2.5 ± 0.2	15		3.3	15	ns
			Figure 1		50		4.2	25	
				3.3 ± 0.3	15		2.3	11	
					50	_	3.0	18	
				5.0 ± 0.5	15	_	1.6	7	
					50	_	2.1	12	
Output disable time		t_{PLZ}, t_{PHZ}	$R_L = 1 k\Omega$	2.5 ± 0.2	15	_	6	15	ns
			Figure 1		50	_	9.6	25	
				3.3 ± 0.3	15	_	4.5	11	
					50	_	7.2	18	
				5.0 ± 0.5	15	_	3.2	7	
					50	_	5.1	12	
Control input capacitance		C _{IN}	All types	_	_	_	2	_	pF
Common terminal capacitance	74VHC4051AFT	C _{IS}	Figure 2	_	_	_	23.4	_	pF
	74VHC4052AFT					_	13.1	_	
	74VHC4053AFT					_	8.2	_	
Switch terminal capacitance	74VHC4051AFT	Cos	Figure 2	_	_	_	5.7	_	pF
	74VHC4052AFT					_	5.6	_	
	74VHC4053AFT					_	5.6	_	
Feedthrough capacitance	74VHC4051AFT	C _{IOS}	Figure 2	_	_	_	0.5	_	pF
	74VHC4052AFT					_	0.5	_	
	74VHC4053AFT					_	0.5		
Power dissipation capacitance	74VHC4051AFT	C _{PD}	Figure 2	_			15		pF
	74VHC4052AFT		(Note 1)				24		
	74VHC4053AFT					_	12	_	

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation.

 $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$



11.5. AC Characteristics (Unless otherwise specified, $T_a = -40$ to 85 °C, Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Max	Unit
Phase difference between input to output	ΦΙ/Ο		2.5 ± 0.2	15	_	16	ns
				50		18	
			3.3 ± 0.3	15		10	
				50	_	12	
			5.0 ± 0.5	15	_	7	
				50		8	
Output enable time	t_{PZL}, t_{PZH}	$R_L = 1 k\Omega$	2.5 ± 0.2	15	_	20	ns
		Figure 1		50	_	32	
			3.3 ± 0.3	15		15	
				50	_	22	
			5.0 ± 0.5	15		10	
				50		16	
Output disable time	t_{PLZ}, t_{PHZ}	$R_L = 1 k\Omega$	2.5 ± 0.2	15	_	23	ns
		Figure 1		50		32	
			3.3 ± 0.3	15		15	
				50	_	22	
			5.0 ± 0.5	15		10	
				50	_	16	
Control input capacitance	C _{IN}	_	_	_	_	10	pF

11.6. AC Characteristics (Unless otherwise specified, $T_a = -40$ to 125 °C, Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Max	Unit
Phase difference between input to output	Φι/Ο		2.5 ± 0.2	15	_	20	ns
				50	_	22	
			3.3 ± 0.3	15	_	13	
				50	_	14	
			5.0 ± 0.5	15	_	9	
				50	_	9.5	
Output enable time	t _{PZL} ,t _{PZH}	$R_L = 1 k\Omega$	2.5 ± 0.2	15	_	23.5	ns
	Figure 1		50	_	37		
			3.3 ± 0.3	15	_	18	
				50	_	25	
			5.0 ± 0.5	15	_	12	
				50	_	19	
Output disable time	t _{PLZ} ,t _{PHZ}	$R_L = 1 k\Omega$	2.5 ± 0.2	15	_	28.5	ns
		Figure 1		50	_	37	
			3.3 ± 0.3	15	_	18	
				50	_	25	
			5.0 ± 0.5	15	_	12	
				50	_	19	
Control input capacitance	C _{IN}	_	_	_	_	10	pF



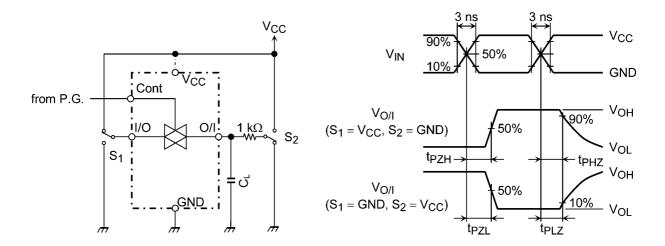
11.7. Analog Switch Characteristics (T_a = 25 °C) (Note)

Characteristics	Part Number	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
Sine Wave Distortion		THD	$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF}$	$V_{IN} = 2.0 V_{p-p}$	3.0	0.1	%
			f _{IN} = 1 kHz	V _{IN} = 4.0 V _{p-p}	4.5	0.03	
Maximum frequency	74VHC4051AFT	f _{MAX(I/O)}			3.0	150	MHz
response	74VHC4052AFT]	Adjust input for 0 dBm. Increase f _{IN} frequency until dB			200	
	74VHC4053AFT		meter reads -3 dB.			240	
	74VHC4051AFT]	$R_L = 50 \Omega$, $C_L = 10 pF$, sine		4.5	180	
	74VHC4052AFT]	wave Figure 3			230	
	74VHC4053AFT		1.194.10			280	
Feed through attenuation (switch OFF)		FTH	V _{IN} is centered at (V _{CC} /2). Adjust input for 0 dBm.		3.0	-45	dB
			$R_L = 600 \Omega$, $C_L = 50 pF$, $f_{IN} = 1 MHz$, sine wave Figure 4		4.5	-45	
			V _{IN} is centered at (V _{CC} /2). Adjust input for 0 dBm.		3.0	-65	
			R_L = 50 Ω , C_L = 10 pF, f_{IN} = 1 MHz, sine wave Figure 4		4.5	-65	
Crosstalk (control input to signal output)		X _{talk}	$R_L = 600 \Omega, C_L = 50 pF,$ $f_{IN} = 1 MHz,$		3.0	60	mV
			square wave (t _r = t _f = 6 ns) Figure 5		4.5	100	
Crosstalk (between any switches)		X _{talk}	V _{IN} is centered at (V _{CC} /2). Adjust input for 0 dBm.		3.0	-45	dB
			$R_L = 600 \Omega$, $C_L = 50 pF$, $f_{IN} = 1 MHz$, sine wave Figure 6		4.5	-45	

Note: These characteristics are determined by design of devices.



12. AC Test Circuit



Cont : Control Inputs A or B or C or INH (C:Except VHC4052A)

P.G. : Pulse generator

Figure 1 tpLZ, tpHZ, tpZL, tpZH

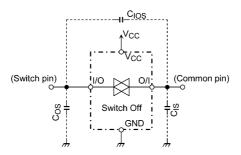


Figure 2 C_{IOS}, C_{IS}, C_{OS}

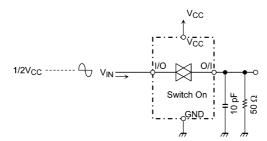


Figure 3 Frequency Response

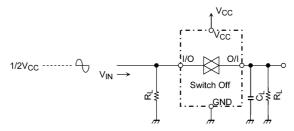
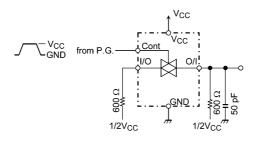


Figure 4 Feedthrough Attenuation

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Cont : Control Inputs A or B or C or INH (C:Except VHC4052A)

P.G. : Pulse generator

Figure 5 Cross Talk (control input to output signal)

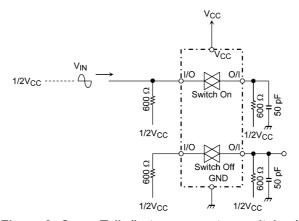
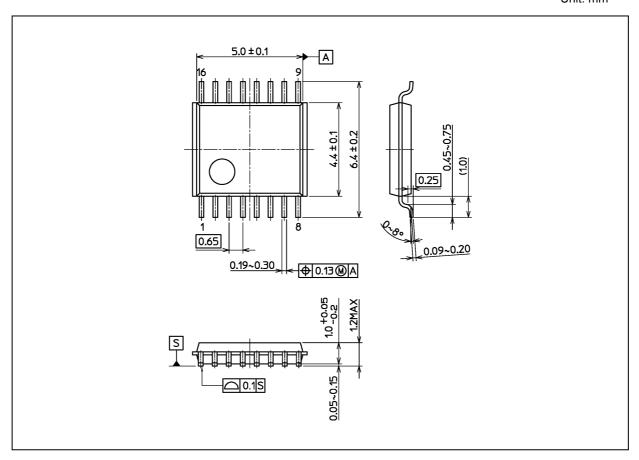


Figure 6 Cross Talk (between any two switches)



Package Dimensions

Unit: mm



Weight: 0.055 g (typ.)

Р	Package Name(s)
Nickname: TSSOP16B	



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